T038N08NNC

RoHS COMPLIANT

80V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
80V	3.8mΩ@10V	115A

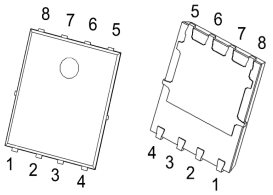
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

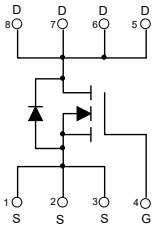
Application

- Power Switching Application
- Motor Driving
- Power Management

PDFN5X6-8L



Schematic diagram



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
T038N08NNC	PDFN5X6-8L	T038N08N	Reel & Tape	330mm	12mm	5000pcs

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1]	T_C = 25°C	I_D	115	A
	T_C = 100°C		73	
Pulsed Drain Current[2]		I_{DM}	460	A
Single Pulsed Avalanche Current[3]		I_{AS}	36	A
Single Pulsed Avalanche Energy[3]		E_{AS}	324	mJ
Power Dissipation[5]	T_C = 25°C	P_D	125	W
Thermal Resistance from Junction to Ambient[6]		$R_{\theta JA}$	52	°C/W
Thermal Resistance from Junction to Case		$R_{\theta JC}$	1.0	°C/W
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55~ +150	°C

Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	80			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[4]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	2.8	4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A		3.8	5.0	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 40V, V_{GS} = 0V, f = 1MHz		3155		pF
Output Capacitance	C_{oss}			616		
Reverse Transfer Capacitance	C_{rss}			24		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 40V, V_{GS} = 10V, I_D = 20A		47		nC
Gate-Source Charge	Q_{gs}			13		
Gate-Drain Charge	Q_{gd}			12		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40V, V_{GS} = 10V, R_G = 3Ω, R_L = 2Ω		16		ns
Turn-On Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(off)}$			32		
Turn-Off Fall Time	t_f			11		
Source-Drain Diode Characteristics						
Diode Forward Voltage[4]	V_{SD}	V_{GS} = 0V, I_S = 20A			1.2	V

Notes:

1.The maximum current rating is limited by package. And device mounted on a large heatsink.

2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.

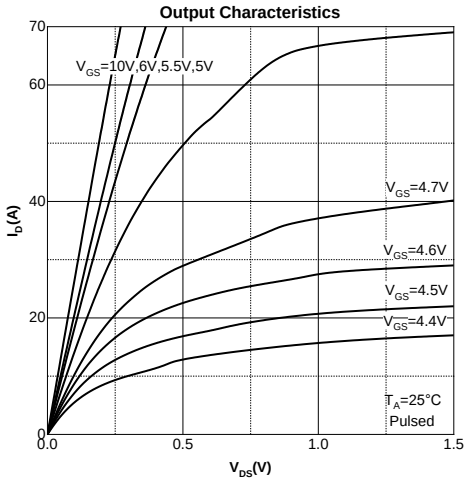
3.E_{AS} condition: V_{DD} = 80V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.

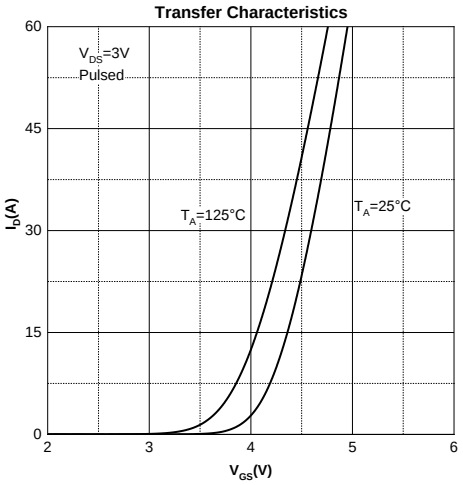
4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.

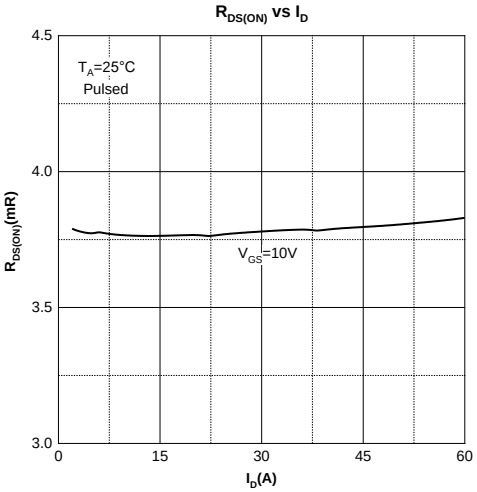
5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C. And device mounted on a large heatsink.

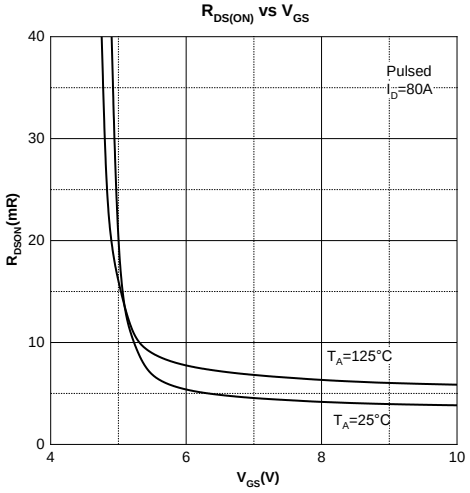
6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

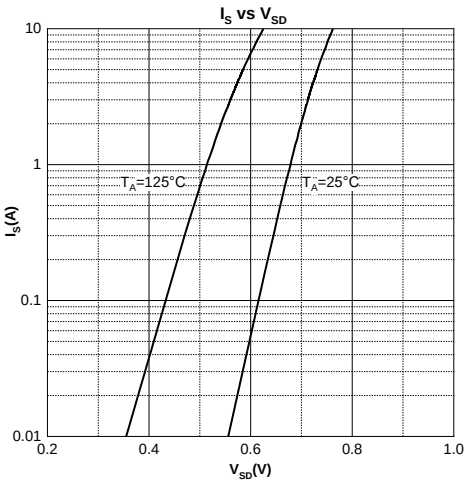
Typical Characteristics

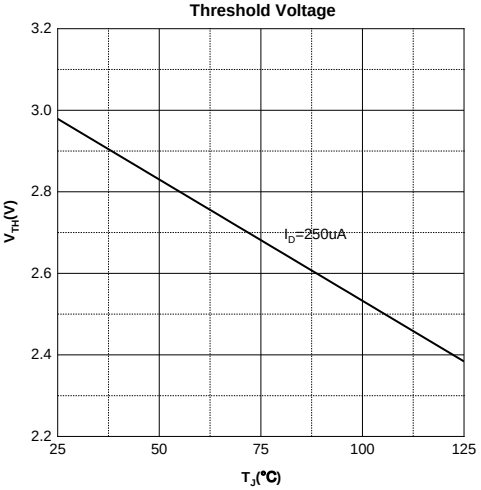




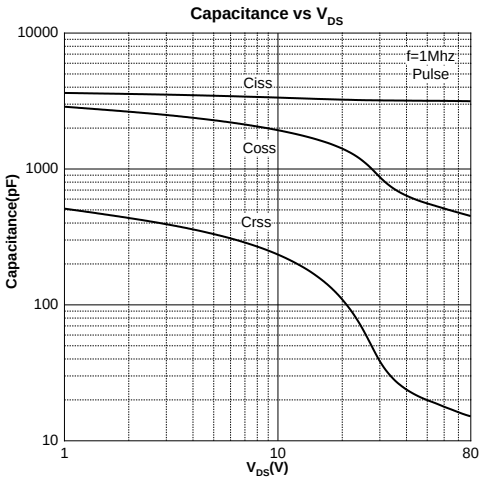


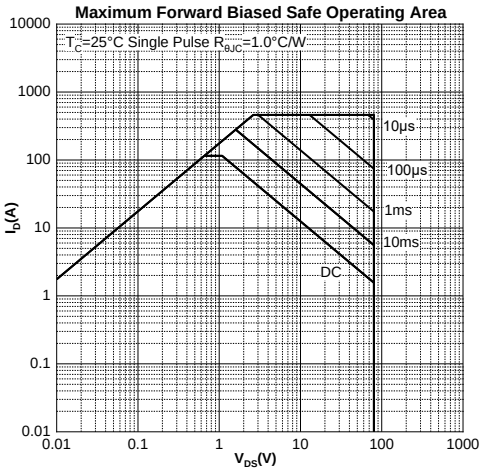


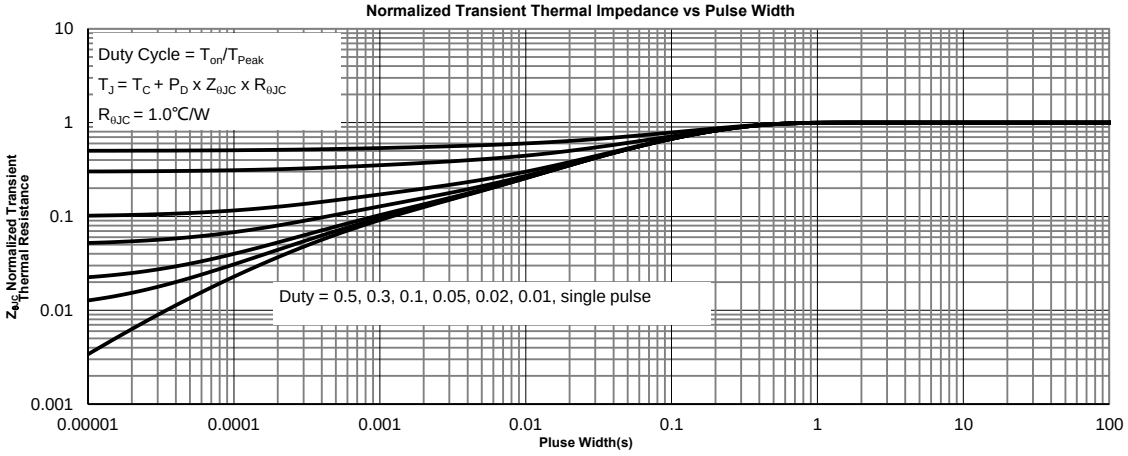




Typical Characteristics

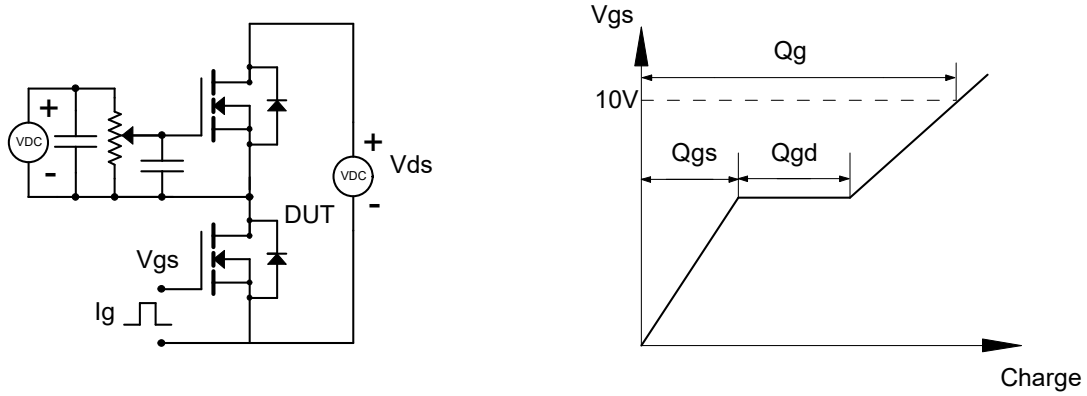




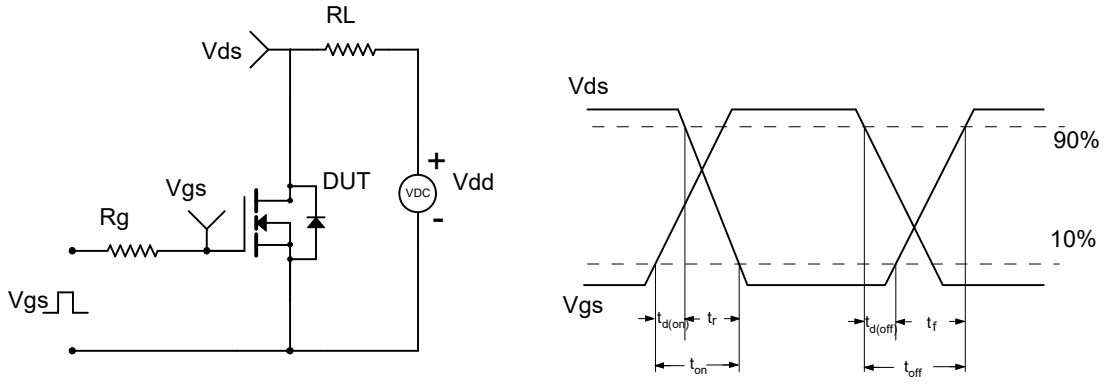


Typical Characteristics

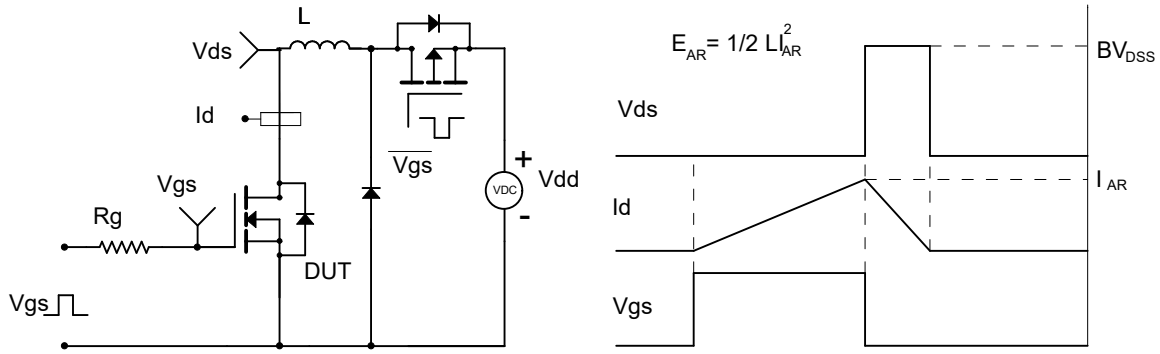
Gate Charge Test Circuit & Waveform

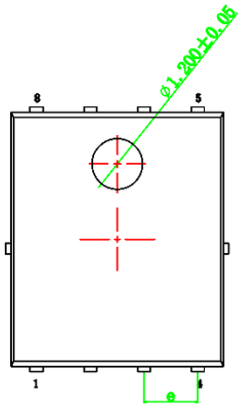


Resistive Switching Test Circuit & Waveform

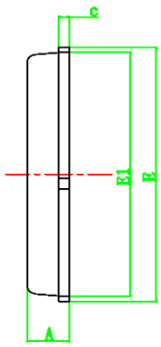


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

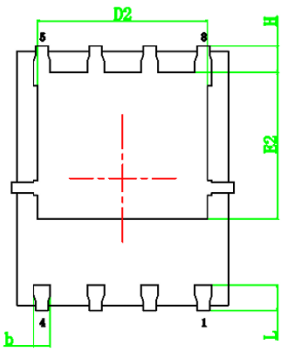




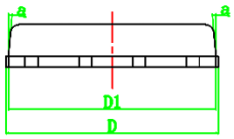
Top View



Side View



Bottom View



Front View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.200	0.035	0.047
b	0.330	0.510	0.013	0.020
c	0.190	0.300	0.007	0.012
D	4.800	5.220	0.189	0.210
D2	3.900	4.300	0.154	0.170
E	5.900	6.100	0.232	0.240
E1	5.700	5.800	0.224	0.228
E2	3.350	3.750	0.132	0.148
e	1.270REF		0.050REF	
H	0.350	0.720	0.014	0.028
D1	4.800	5.000	0.189	0.197
L	0.350	0.750	0.014	0.030
a	0°	12°	0°	12°